Description

The VSM101P06 uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g. This device is ideal for high-frequency switching and synchronous rectification

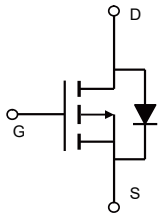
Application

- High-frequency Switching and Synchronous Rectification
- DC/DC and AC/DC Converter
- Motor Driver
- Battery Management System (BMS)

General Features

- V_{DS} =-60V,I_D =-101A
  $R_{DS(ON)}$=6.7mΩ (typical) @ V_{GS}=-10V
  $R_{DS(ON)}$=8.8mΩ (typical) @ V_{GS}=-4.5V
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 175°C operating temperature
- Pb-free lead plating

TO-220



Schematic

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VSM101P06	VSM101P06-TC	TO-220	-	-	-

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	-101	A
Drain Current-Continuous(T_C=100℃)	I_D (100℃)	-71	A
Pulsed Drain Current	I_{DM}	-404	A
Maximum Power Dissipation	P_D	180	W
Derating factor		1.2	W/℃
Single pulse avalanche energy (Note 1)	E_{AS}	615	mJ
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 175	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Case	$R_{\theta JC}$	0.83	℃/W
Thermal Resistance,Junction-to-Ambient (Note 4)	$R_{\theta JA}$	40	℃/W

Electrical Characteristics (T_C=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=-250μA	-60	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-60V,V_{GS}=0V	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250μA	-1.0	-1.6	-2.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_D=-20A	-	6.7	10.0	mΩ
		V_{GS}=-4.5V, I_D=-20A	-	8.8	12.0	mΩ
Gate resistance	R_G	F=1.0MHz	-	4.5	-	Ω
Forward Transconductance	g_{FS}	V_{DS}=-10V,I_D=-20A	-	60	-	S
Dynamic Characteristics						
Input Capacitance	C_{lss}	V_{DS}=-30V,V_{GS}=0V, F=1.0MHz	-	4291	-	pF
Output Capacitance	C_{oss}		-	643	-	pF
Reverse Transfer Capacitance	C_{rss}		-	23.6	-	PF
Switching Characteristics (Note 2)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=-30V,I_D=-20A V_{GS}=-10V,R_G=1.6Ω	-	15	-	nS
Turn-on Rise Time	t_r		-	18	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	50	-	nS
Turn-Off Fall Time	t_f		-	18	-	nS
Total Gate Charge	Q_g	V_{DS}=-30V,I_D=-20A, V_{GS}=-10V	-	67	-	nC
Gate-Source Charge	Q_{gs}		-	9.0	-	nC
Gate-Drain Charge	Q_{gd}		-	9.1	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	V_{GS}=0V,I_S=-20A	-	-	-1.2	V
Diode Forward Current	I_S		-	-	-101	A
Reverse Recovery Time	t_{rr}	T_J = 25°C, I_F =-20A di/dt = 100A/μs	-	55	-	nS
Reverse Recovery Charge	Qrr		-	101	-	nC

Notes:

1. EAS condition : Tj=25℃,V_{DD}=-30V,V_G=-10V,L=0.5mH,Rg=25Ω
2. Guaranteed by design, not subject to production
3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsin k, assuming a maximum junction temperature of TJ(MAX)=175°C. The SOA curve provides a single pulse rating.
4. The value of $R_{\theta JA}$ is measured with the device mounted on 1in2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The maximum allowed junction temperature of 175°C. The value in any given application depends on the user's specific board design, and the maximum temperature of 150°C may be used if the PCB allows it.

Typical Electrical and Thermal Characteristics

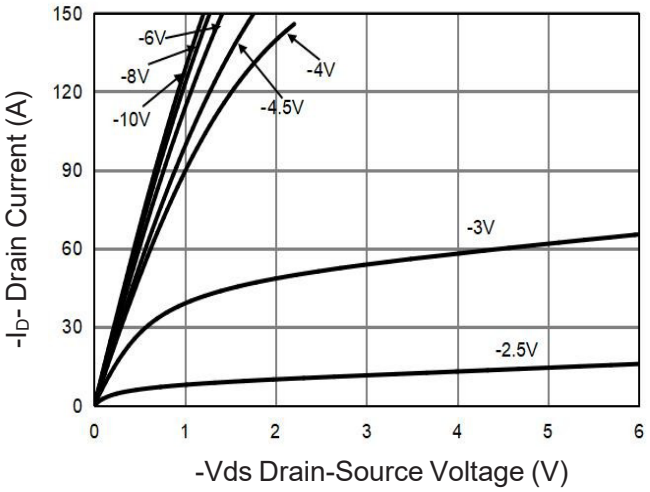


Figure 1 Output Characteristics

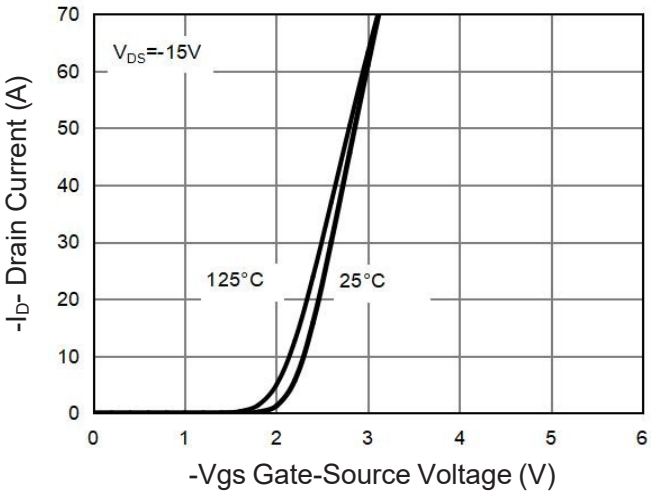


Figure 2 Transfer Characteristics

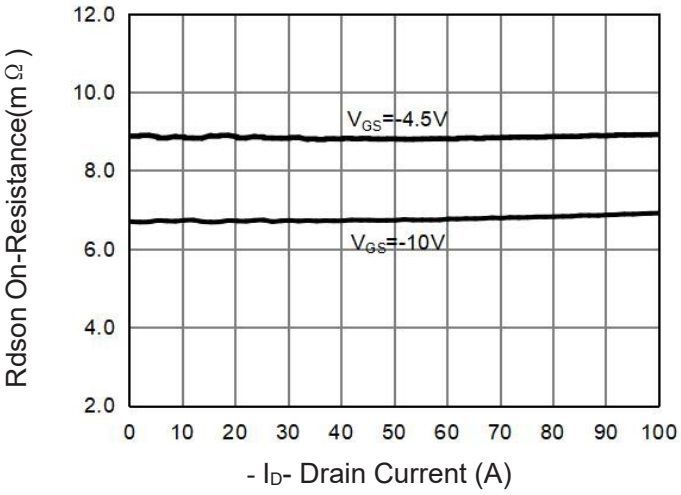


Figure 3 Rdson- Drain Current

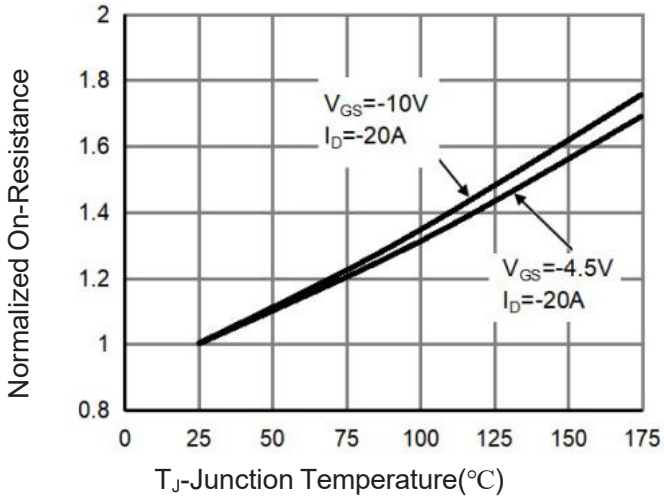


Figure 4 Rdson-JunctionTemperature

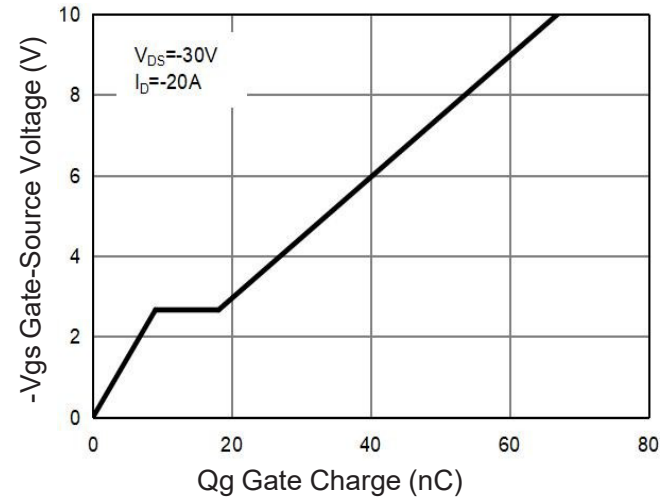


Figure 5 Gate Charge

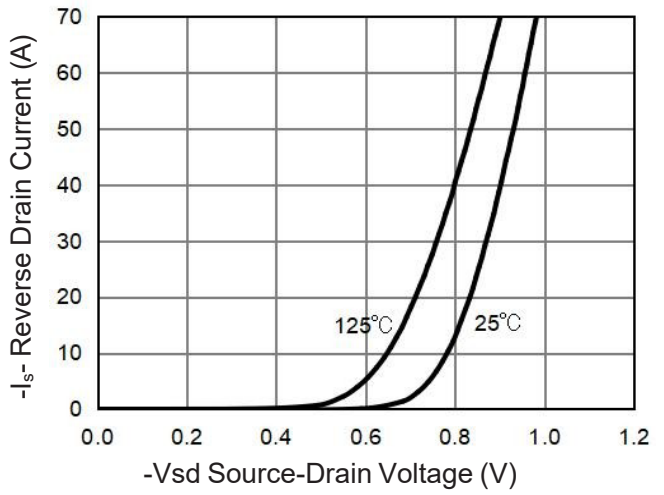


Figure 6 Source- Drain Diode Forward

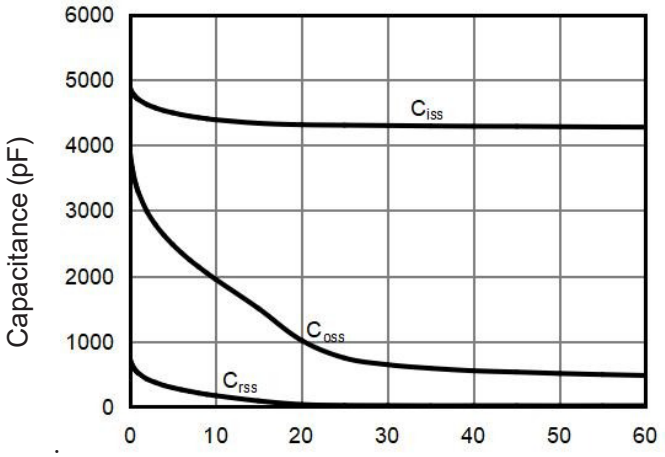


Figure 7 Capacitance vs Vds

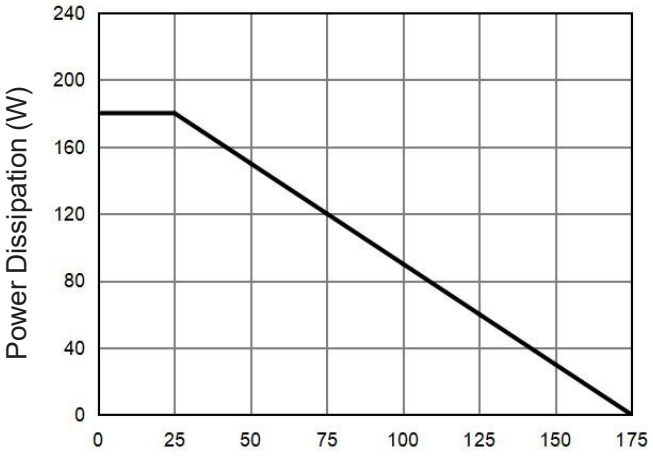


Figure 9 Power De-rating

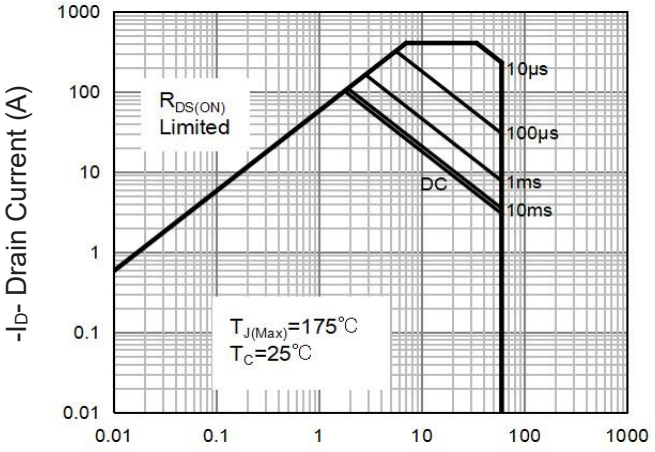


Figure 8 Safe Operation Area(Note 3)

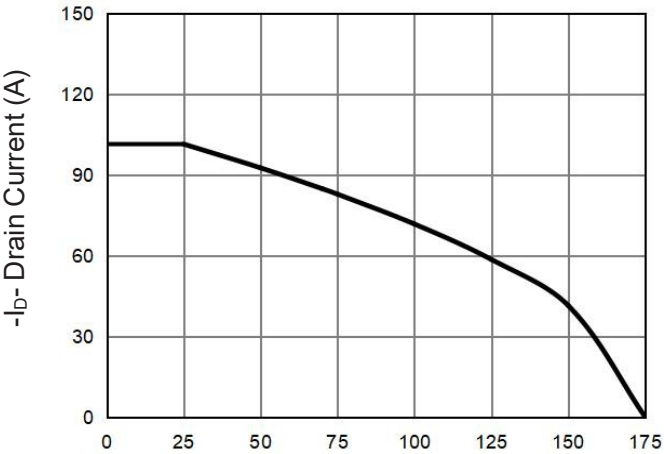


Figure 10 Current De-rating

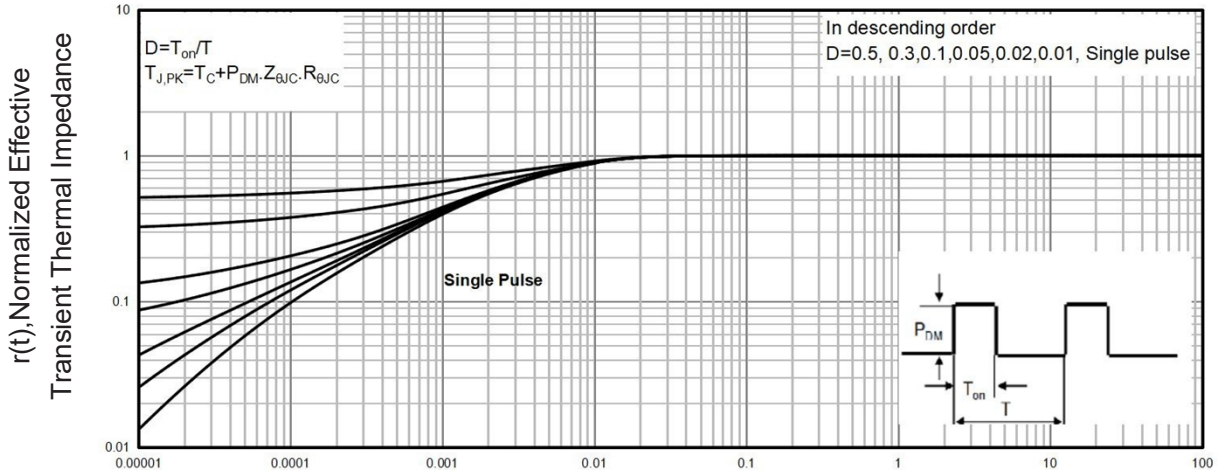


Figure 11 Normalized Maximum Transient Thermal Impedance